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ATTY. DOCKET NO.
501.22642CC9

SERIAL NO.

APPLICANT
FUJISAKI et al

FILING DATE
July 23, 2003

GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
SWC	4 5 4 4 4 1 7	10/85	Clarke			
	4 6 1 8 3 9 6	10/86	Shimoda			
	3 8 3 3 3 4 2	9/74	Holliday			
	3 4 4 6 6 0 3	5/69	Lolacono			
	3 0 3 3 6 6 0	5/62	Okkerse			
	4 2 9 9 6 5 0	11/81	Bonner			
	2 9 0 8 0 0 4	10/59	Levinson			
	4 5 3 9 0 6 7	9/85	Washizuka			
	4 5 8 6 9 7 9	5/86	Katsumata			
	4 6 3 7 8 5 4	1/87	Fukuda			
SWC	4 6 4 5 5 6 0	2/87	Matsumoto			

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
					YES NO
SWC 55 1 1 3 6 9 9	9/80	Japan			X

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

SWC	Ghandhi, S. VLSI Fabrication Principles, John Wiley, 1983 pp 86-90, 98-100
SWC	Sze, S., Physics of Semiconductor Devices, John Wiley, 1981, p 33
SWC	IEEE Transactions on Electron Devices, vo. ED-31, No. 8, Aug. 1984, pp 1057, para 4 5; New York, US; S. Miyazawa

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EXAMINER: Initial if citation is considered, draw line through citation if not in compliance and not considered. Include copy of this form with next communication to applicant.

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U.S. PATENT DOCUMENTS

[illegible]

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

SWC	Journal of Crystal Growth, Vol. 63 no. 2, Oct. 1983 pp 415-418, Amsterdam NL; Fornari "Dislocation-free silicon-doped gallium arsenide grown by LEC Procedure"
}	Terashima "Control of Growth Parameters for Obtaining Highly Uniform Large Diameter LEC GaAs" 5th Conf. On Semi-insulating III-V Materials, 1988 pp 413-422
	Matsuoko et al "uniformity Evaluation of MESFETs for FGaAs LSI Fabrication" IEEE Trans. On Elec. Dev. Vol ED31, no. 8 Aug. 1984 pp 1062
}	Applied Physics Letters, vol 44, no. 1, Jan. 1984 pp 74-76 New York, US; Hunter "Carbon in Semi-Insulating, liquid Encapsulated Czochralski GaAs"
	Patent Abstracts of Japan, vol, 4, no. 173 (C-32) [655], 29 Nov. 1980; JP A-55-113-669 Sumitomo 2-09-1980

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